

Generation of parabolic similaritons in tapered silicon photonic wires: comparison of pulse dynamics at telecom and mid-IR wavelengths

Spyros Lavdas,^{1,*} Jeffrey B. Driscoll,² Hongyi Jiang,¹ Richard R. Grote,²
Richard M. Osgood, Jr.,² and Nicolae C. Panoiu¹

¹*Department of Electronic and Electrical Engineering, University College London, Torrington Place, London WC1E 7JE, UK*

²*Microelectronics Sciences Laboratories, Columbia University, New York, NY 10027, USA*

*Corresponding author: *s.lavdas@ucl.ac.uk*

We study the generation of parabolic self-similar optical pulses in tapered Si photonic nanowires (Si-PhNWs) both at telecom ($\lambda = 1.55 \mu\text{m}$) and mid-IR ($\lambda = 2.2 \mu\text{m}$) wavelengths. Our computational study is based on a rigorous theoretical model, which fully describes the influence of linear and nonlinear optical effects on pulse propagation in Si-PhNWs with arbitrarily varying width. Numerical simulations demonstrate that, in the normal dispersion regime, optical pulses evolve naturally into parabolic pulses upon propagating in millimeter-long tapered Si-PhNWs, with the efficiency of this pulse reshaping process being strongly dependent on the spectral and pulse parameter regime in which the device operates, as well as the particular shape of the Si-PhNW. © 2021 Optical Society of America

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Generation of pulses with specific spectral and temporal characteristics is a key functionality needed in many applications in ultrafast optics, optical signal processing, and optical communications. One type of such pulses, which can be used as primary information carriers in optical communications systems, are pulses that preserve their shape upon propagation. Solitons are the most ubiquitous example of such a pulse that form in the anomalous group-velocity dispersion (GVD) regime, whereas their counterpart in the normal GVD region are self-similar pulses, called similaritons [1–3]. Unlike solitons, which require a threshold power, no constraints have to be imposed on the pulse energy, initial shape, or optical phase profile to generate similaritons. Due to their self-similar propagation, similaritons do not undergo wave breaking and the linear chirp they acquire during their formation makes it easy to employ dispersive pulse compression techniques to generate nearly transform-limited pulses. These remarkable properties of similaritons have provided a strong incentive for their study, and optical similaritons have been demonstrated in active optical fiber systems such as Yb-doped fiber amplifiers [3, 4], using passive schemes based on dispersion-managed or tapered silica fibers [5–8], and high-power fiber amplifiers [9–11].

Driven by the ever growing demand for enhanced integration of complex optoelectronic architectures that process increasing amounts of data, finding efficient ways to extend the regime of self-similar pulse propagation to chip-scale photonic devices is becoming more pressing. One promising approach, based on silicon (Si) fibers with micrometer-sized core dimensions [12], has recently been proposed [13]. A further degree of device integration can be achieved by employing Si photonic nanowires (Si-PhNWs) with submicrometer transverse size fabricated on a silicon-on-insulator material system [14]. In addition to the enhanced optical nonlinearity and strong fre-

quency dispersion, which allows for increased device integration, Si-PhNWs allow for seamless integration with complementary metal-oxide semiconductor technologies. Importantly, the use of Si-PhNWs can be extended to the mid-infrared (mid-IR) spectral region ($\lambda \gtrsim 2.2 \mu\text{m}$) [15], where Si provides superior functionality due to low two-photon absorption (TPA) and consequently reduced free-carrier absorption (FCA). In fact, it has already been shown that nonlinear optical effects such as modulational instability [16, 17], frequency dispersion of the nonlinearity [18], and supercontinuum generation [17, 19–21], can be used to achieve significant pulse reshaping in millimeter-long Si-PhNWs (for a review, see [22]).

In this Letter, we use a rigorous theoretical model, which describes the propagation of pulses in Si-PhNWs, and comprehensive numerical simulations to demonstrate that optical similaritons with parabolic shape can be generated in millimeter-long, dispersion engineered Si-PhNWs. In order to gain a better understanding of the underlying physics of similariton generation, we present a comparative analysis of the pulse dynamics in two spectral domains relevant for technological applications, namely telecom ($\lambda = 1.55 \mu\text{m}$) and mid-IR ($\lambda = 2.2 \mu\text{m}$) spectral regions. Thus, the pulse dynamics are described by the following equation [18, 23–25]:

$$i \frac{\partial u}{\partial z} + \sum_{n \geq 1} \frac{i^n \beta_n(z)}{n!} \frac{\partial^n u}{\partial t^n} = - \frac{ic\kappa(z)}{2nv_g(z)} \alpha_{\text{FC}}(z)u - \frac{\omega\kappa(z)}{nv_g(z)} \delta n_{\text{FC}}(z)u - \gamma(z) \left[1 + i\tau(z) \frac{\partial}{\partial t} \right] |u|^2 u, \quad (1)$$

where $u(z, t)$ is the pulse envelope, z and t are the distance along the Si-PhNW and time, respectively, $\beta_n(z) = d^n \beta / d\omega^n$ is the n th order dispersion coefficient, $\kappa(z)$ quantifies the overlap between the optical mode and the active area of the waveguide, $v_g(z)$ is the group-velocity, $\delta n_{\text{FC}}(z)$ [$\alpha_{\text{FC}}(z)$] are the free-carrier

(FC) induced index change (losses) and are given by $\delta n_{\text{FC}}(z) = -e^2/2\epsilon_0 n \omega^2 [N(z)/m_{ce}^* + N(z)^{0.8}/m_{ch}^*]$ and $\alpha_{\text{FC}}(z) = e^3 N(z)/\epsilon_0 c n \omega^2 (1/\mu_e m_{ce}^{*2} + 1/\mu_h m_{ch}^{*2})$, respectively, where N is the FC density, $m_{ce}^* = 0.26m_0$ ($m_{ch}^* = 0.39m_0$) is the effective mass of the electrons (holes), with m_0 the mass of the electron, and μ_e (μ_h) the electron (hole) mobility. The nonlinear properties of the waveguide are described by the nonlinear coefficient, $\gamma(z) = 3\omega P_0 \Gamma(z)/4\epsilon_0 A(z)v_g^2(z)$, and the shock time scale, *i.e.* the characteristic response time of the nonlinearity, $\tau(z) = \partial \ln \gamma(z)/\partial \omega$, where P_0 is the peak power of the input pulse, and $A(z)$ and $\Gamma(z)$ are the cross-sectional area and the effective third-order susceptibility of the waveguide, respectively. Our model is completed by a rate equation describing the FC dynamics,

$$\frac{\partial N}{\partial t} = -\frac{N}{t_c} + \frac{3P_0^2 \Gamma''(z)}{4\epsilon_0 \hbar A^2(z) v_g^2(z)} |u|^4, \quad (2)$$

where Γ'' (Γ') is the imaginary (real) part of Γ .

The system (1)-(2) provides a rigorous description of pulse propagation in Si-PhNWs with adiabatically varying transverse size since the z -dependence of the waveguide parameters is fully incorporated in our model *via* the implicit dependence of the modes of the Si-PhNW on its transverse size. Thus, we consider a tapered ridge waveguide with a Si rectangular core buried in SiO_2 , with height, $h = 250$ nm, and width, w , varying from w_{in} to w_{out} between the input and output facets, respectively. Using a finite-element mode solver we determine the propagation constant, $\beta(\lambda)$, and the fundamental TE-like mode, for $1.3 \mu\text{m} \leq \lambda \leq 2.3 \mu\text{m}$ and for 51 values of the waveguide width ranging from 500 nm to 1500 nm. The dispersion coefficients are calculated by fitting $\beta(\lambda)$ with a 12th order polynomial and subsequently calculating the corresponding derivatives with respect to ω .

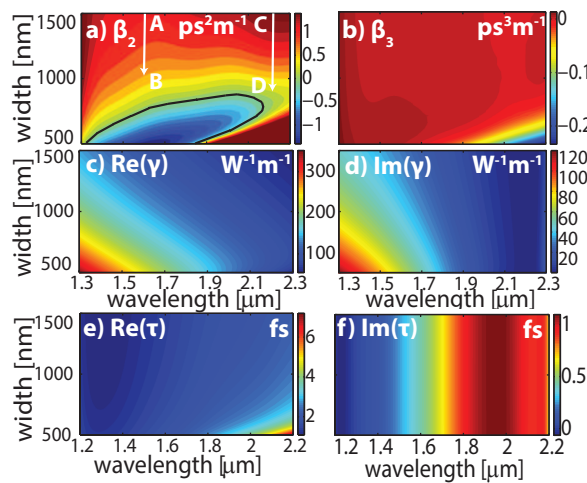


Fig. 1. Dispersion maps of a) β_2 , b) β_3 , c) self-phase modulation coefficient, γ' , d) TPA coefficient, γ'' , and e) real and f) imaginary part of the shock-time coefficient, τ . In a), $\beta_2 = 0$ on the black contour and arrows indicate the limits of w , at $\lambda = 1.55 \mu\text{m}$ and $\lambda = 2.2 \mu\text{m}$.

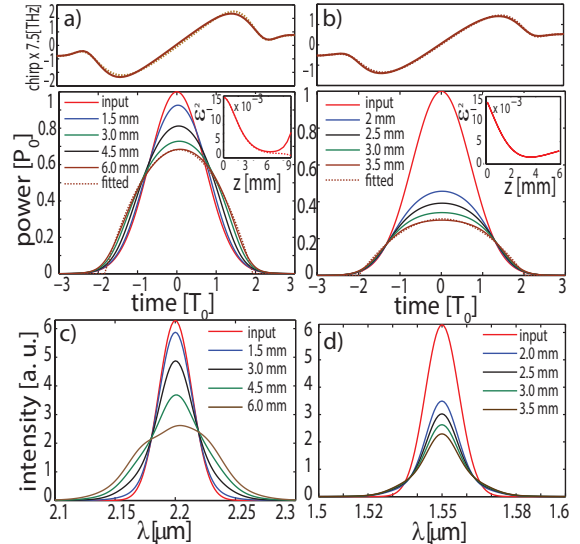


Fig. 2. Temporal pulse shape with increasing z and the chirp of the output pulse, calculated for the full model (solid line) and for $\beta_3 = 0$ and $\tau = 0$ (dotted line) (top panels) and the corresponding pulse spectra (bottom panels). In insets, ϵ_I^2 vs. z , for the full model (solid line) and for $\beta_3 = 0$ and $\tau = 0$ (dotted line). Left (right) panels correspond to $\lambda = 2.2 \mu\text{m}$ ($\lambda = 1.55 \mu\text{m}$).

Using these results and the corresponding optical modes, the waveguide parameters, κ , γ , and τ , are computed for all values of w . The z -dependence of these parameters is then determined by polynomial interpolation.

The results of this analysis are summarized in Fig. 1, where we plot the dispersion maps of the waveguide parameters. Thus, Fig. 1(a) shows that if $w < 887$ nm the Si-PhNW has two zero GVD wavelengths, defined by $\beta_2(\lambda, w) = 0$, whereas if $w > 887$ nm the Si-PhNW has normal GVD in the entire spectral domain. In addition, if $\lambda > 2187$ nm the waveguide has normal GVD for any w . Important properties of the Si-PhNW are revealed by the dispersion maps of the nonlinear coefficients as well. Specifically, the strength of the nonlinearity, $\gamma'(\lambda, w)$, decreases with both increasing w and λ , meaning that in the range of wavelengths and waveguide widths explored here, nonlinear effects in Si-PhNWs are stronger if narrow waveguides are used at lower wavelengths. On the other hand the TPA coefficient, $\gamma''(\lambda, w)$, and consequently nonlinear losses, decrease with w and λ , which suggests that the waveguide parameters and wavelength must be properly chosen for optimum device operation. Finally, as seen in Fig. 1(e), the shock time $\tau'(\lambda, w)$ has large values at long wavelengths but decreases with w .

To investigate the formation of self-similar pulses, we considered first a Gaussian pulse, $u(t) = e^{-t^2/2T_0^2}$ with full-width at half-maximum (FWHM) $T_{\text{FWHM}} = 220$ fs ($T_{\text{FWHM}} = 1.665T_0$), and peak power $P_0 = 7$ W, which is launched in an exponentially tapered Si-PhNW, $w(z) = w_{\text{in}} e^{-az}$, with $w_{\text{in}} = 1500$ nm. The remaining parameters are: *i*) at $\lambda = 1.55 \mu\text{m}$, $w_{\text{out}} = 1080$ nm,

$\beta_{2,\text{in}} = 1.11 \text{ ps}^2\text{m}^{-1}$, $\beta_{2,\text{out}} = 0.79 \text{ ps}^2\text{m}^{-1}$, and length, $L = 3.5 \text{ mm}$ [arrow $A - B$ in Fig. 1(a)], and ii) at $\lambda = 2.2 \text{ }\mu\text{m}$, $w_{\text{out}} = 850 \text{ nm}$, $\beta_{2,\text{in}} = 1.53 \text{ ps}^2\text{m}^{-1}$, $\beta_{2,\text{out}} = 0.088 \text{ ps}^2\text{m}^{-1}$, and $L = 6 \text{ mm}$ [arrow $C - D$ in Fig. 1(a)]. In Fig. 2 we plot the pulse profile and its spectrum, calculated for several values of z . As expected, the pulse decay is stronger at $\lambda = 1.55 \text{ }\mu\text{m}$ as compared to that at $\lambda = 2.2 \text{ }\mu\text{m}$, due to larger TPA. The stronger nonlinear effects at $\lambda = 2.2 \text{ }\mu\text{m}$ are also revealed by the spectral ripples that start to form at $z \gtrsim 5 \text{ mm}$ (no such modulations are seen at $\lambda = 1.55 \text{ }\mu\text{m}$). Also, the pulse becomes more asymmetric at $\lambda = 2.2 \text{ }\mu\text{m}$, due to increased τ [18]. However, the most important phenomenon revealed by Fig. 2 is that at both wavelengths the pulse evolves into a parabolic one, $|u_p(t)|^2 = |u_p(t_0)|^2[1 - (t - t_0)^2/T_p^2]$ for $|t - t_0| < T_p$ and $u_p(t) = 0$ otherwise, where $u_p(t_0)$, t_0 , and T_p are the amplitude, time shift, and pulse width, respectively.

The generation of parabolic pulses can be quantitatively characterized by the intensity misfit parameter, ε_I^2 , which provides a global measure of how close the pulse profile is to a parabolic one; it is defined as:

$$\varepsilon_I^2 = \frac{\int [|u(t)|^2 - |u_p(t)|^2]^2 dt}{\int |u(t)|^4 dt}. \quad (3)$$

The inset plots in Figs. 2(a) and 2(b) show that at both wavelengths there is a certain optimum waveguide length at which ε_I^2 reaches a minimum value, namely $\varepsilon_I^2 = 1.67 \times 10^{-3}$ ($\varepsilon_I^2 = 1.57 \times 10^{-3}$) at $\lambda = 2.2 \text{ }\mu\text{m}$ ($\lambda = 1.55 \text{ }\mu\text{m}$). The small values of ε_I^2 provide clear evidence of the formation of parabolic pulses. The pulse becomes closer to a parabolic pulse at $\lambda = 1.55 \text{ }\mu\text{m}$ because the effects that induce pulse asymmetry, namely the third-order dispersion and nonlinearity dispersion, are smaller at this wavelength. This can also be seen by comparing the dependence $\varepsilon_I^2(z)$ in the case of the full model (1)-(2) and when higher-order effects are neglected ($\beta_3 = 0$ and $\tau = 0$). Thus, at $\lambda = 1.55 \text{ }\mu\text{m}$, $\varepsilon_I^2(z)$ is almost unaffected if one neglects higher-order effects, whereas in the same conditions, at $\lambda = 2.2 \text{ }\mu\text{m}$, the minimum of $\varepsilon_I^2(z)$ decreases considerably to 0.41×10^{-3} (and is reached at $z = 9.52 \text{ mm}$).

A fundamental characteristic of parabolic pulses is that across the pulse the frequency chirp varies linearly with time. The pulses generated in our numerical experiments clearly have this property, as illustrated in the top panels of Figs. 2(a) and 2(b). These figures also show that, at both wavelengths, this linear time dependence of the chirp is preserved even in the presence of higher-order effects, which demonstrates the robustness against perturbations of the parabolic pulse generation.

The dependence of the similariton generation on the pulse parameters is particularly important when assessing the effectiveness of this optical process. In order to study this dependence, we have determined ε_I^2 , at both wavelengths, as a function of pulse parameters, T_{FWHM} and P_0 . The results of our analysis, summarized in Fig. 3, show that for a given waveguide length there is an

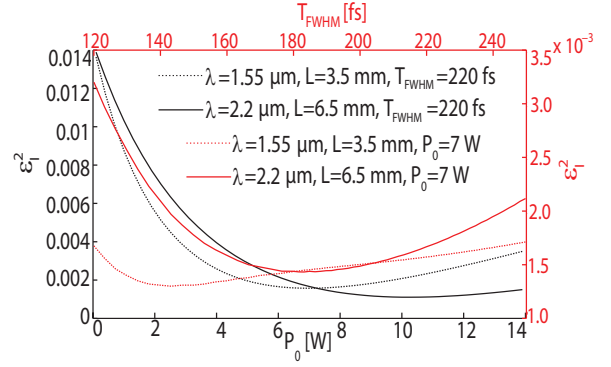


Fig. 3. Dependence of ε_I^2 on pulse width and power.

optimum power at which ε_I^2 reaches a minimum, which is explained by the fact that the similariton formation length increases with P_0 . By contrast, there is no optimum value of T_{FWHM} at which ε_I^2 becomes minimum.

The relation between the input pulse parameters and the similariton generation can be further explored by considering pulses with different shapes. Our results regarding this dependence are summarized in Fig. 4, where we plot the evolution of $\varepsilon_I^2(z)$, determined for varying P_0 . As input pulses we considered a Gaussian pulse, a supergaussian pulse, $u(t) = e^{-t^{2m}/2T_0^{2m}}$ with $m = 2$ ($T_{\text{FWHM}} = 1.824T_0$), and a sech pulse, $u(t) = \text{sech}(t/T_0)$, where $T_{\text{FWHM}} = 1.763T_0$. In all cases $T_{\text{FWHM}} = 220 \text{ fs}$. There are several revealing conclusions that can be drawn from the maps in Fig. 4. First, the Gaussian pulse leads to the lowest values of $\varepsilon_I^2(z)$, which suggests that this pulse shape is the most efficient one for generating similaritons. Second, in the case of Gaussian and sech pulses there is a band of low values of $\varepsilon_I^2(z)$, which is narrower at $\lambda = 1.55 \text{ }\mu\text{m}$ as compared to its width at

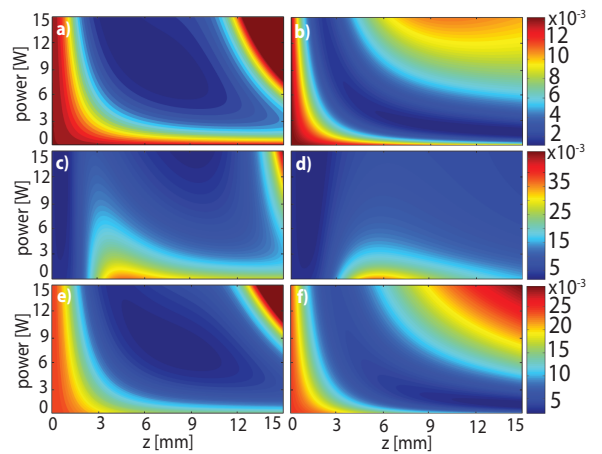


Fig. 4. Dependence of ε_I^2 on z and pulse power, calculated for a Gaussian pulse (top panels), supergaussian with $m = 2$ (middle panels), and sech pulse (bottom panels). In all cases $T_{\text{FWHM}} = 220 \text{ fs}$. Left (right) panels correspond to $\lambda = 2.2 \text{ }\mu\text{m}$ ($\lambda = 1.55 \text{ }\mu\text{m}$).

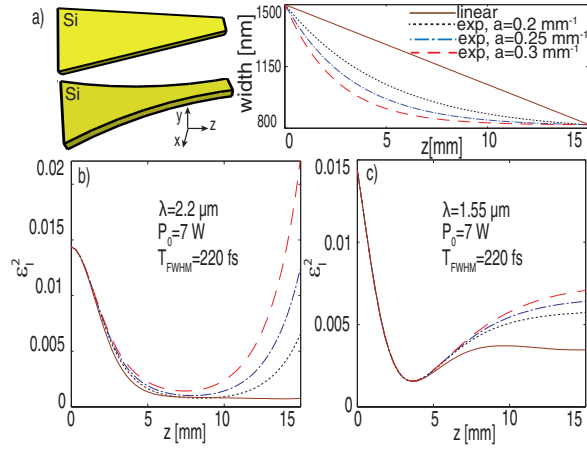


Fig. 5. a) Schematics and dependence $w(z)$ for a linear taper and exponential ones, $w(z) = w_{\text{in}} + (w_{\text{out}} - w_{\text{in}})(1 - e^{-az})/(1 - e^{-aL})$. In all cases $w_{\text{in}} = 1500$ nm and $w_{\text{out}} = 820$ nm. b) and c) show the evolution of ε_I^2 vs. z , for the tapers in a), at $\lambda = 2.2 \mu\text{m}$ and $\lambda = 1.55 \mu\text{m}$, respectively.

$\lambda = 2.2 \mu\text{m}$ and in both cases it broadens as P_0 decreases, whereas in the case of supergaussian pulses two such bands exist. Finally, pulses with a supergaussian shape evolve into a similariton over the shortest distance, which is explained by the fact that of the three pulse profiles the supergaussian one is closest to a parabolic pulse.

Due to its practical relevance, we also studied the generation of similaritons in Si-PhNW tapers with different profiles. To this end, we considered a linear taper and exponential ones with different z -variation rate, in all cases the (Gaussian) pulse parameters and w_{in} and w_{out} being the same [see Fig. 5(a)]. The results of this analysis, which are presented in Fig. 5, show that although similaritons are generated irrespective of the taper profile, the efficiency of this process does depend on the shape of the taper. In particular, overall the linear taper is the most effective for similariton generation, whereas in the case of exponential tapers the steeper their profile the more inefficient they are. These conclusions qualitatively remain valid at both $\lambda = 2.2 \mu\text{m}$ and $\lambda = 1.55 \mu\text{m}$, although the overall pulse dynamics do depend on wavelength. In particular, ε_I^2 is smaller at $\lambda = 2.2 \mu\text{m}$ and the pulse preserves a parabolic shape for a longer distance, in agreement with the results in Fig. 4.

In conclusion, we have demonstrated that parabolic pulses can be generated in millimeter-long tapered Si-PhNWs with engineered decreasing normal GVD. Our analysis showed that using this approach optical similaritons can be generated at both telecom and mid-IR wavelengths, irrespective of the pulse shape and taper profile. However, our investigations have revealed that the efficiency of the similariton generation is strongly dependent on the wavelength at which the device operates, pulse parameters and its temporal profile, as well as the particular shape of the Si-PhNW taper.

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